

FIG. 2

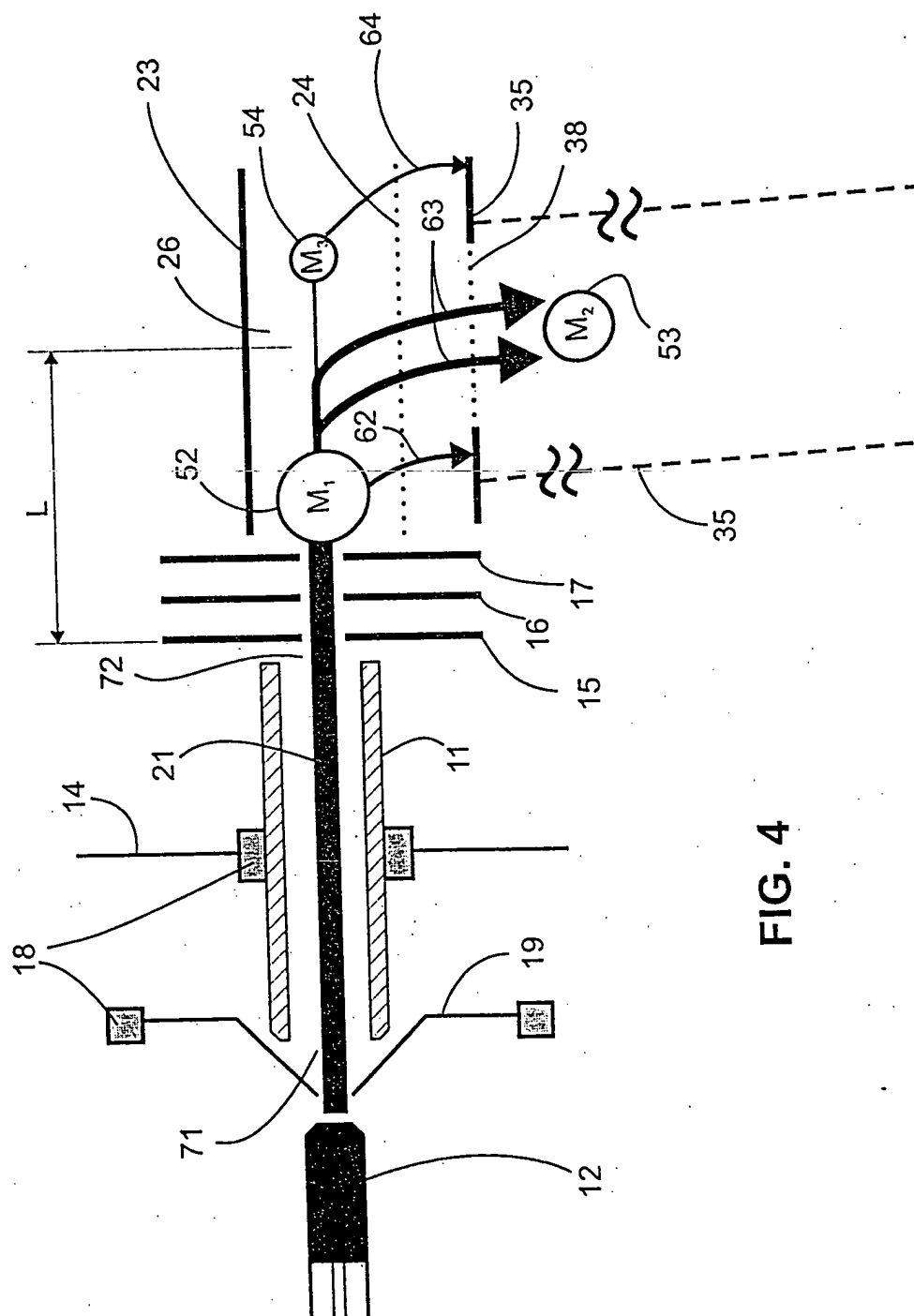


FIG. 4

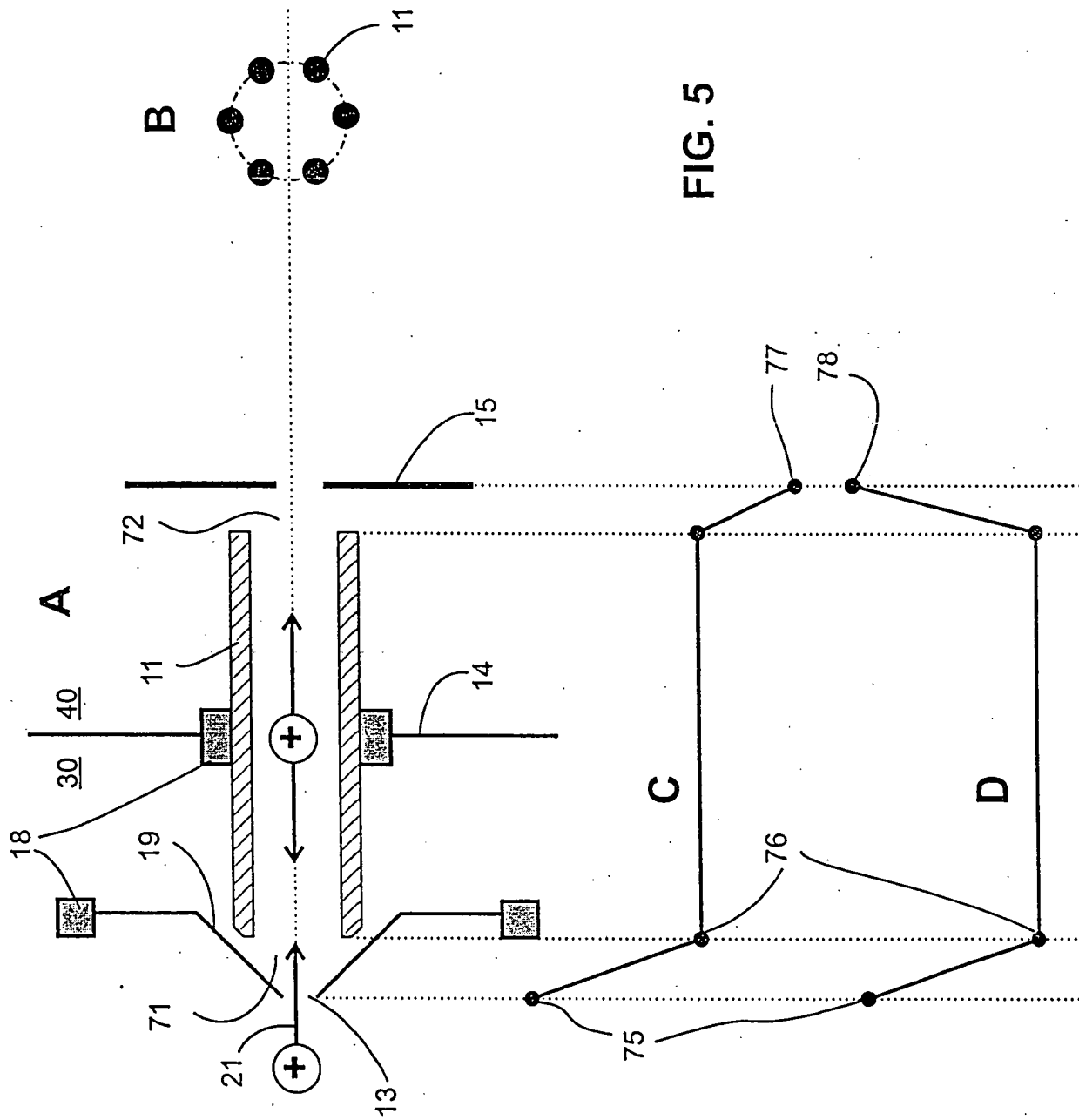


FIG. 5

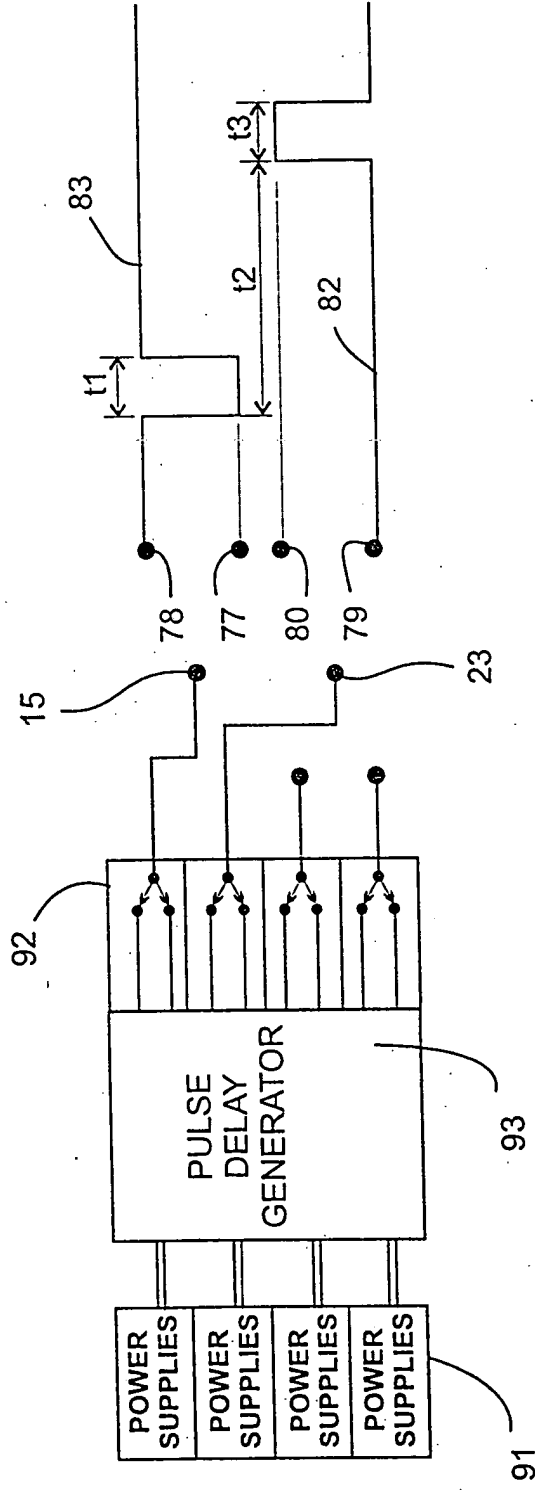


FIG. 6

REF ID: A9430350

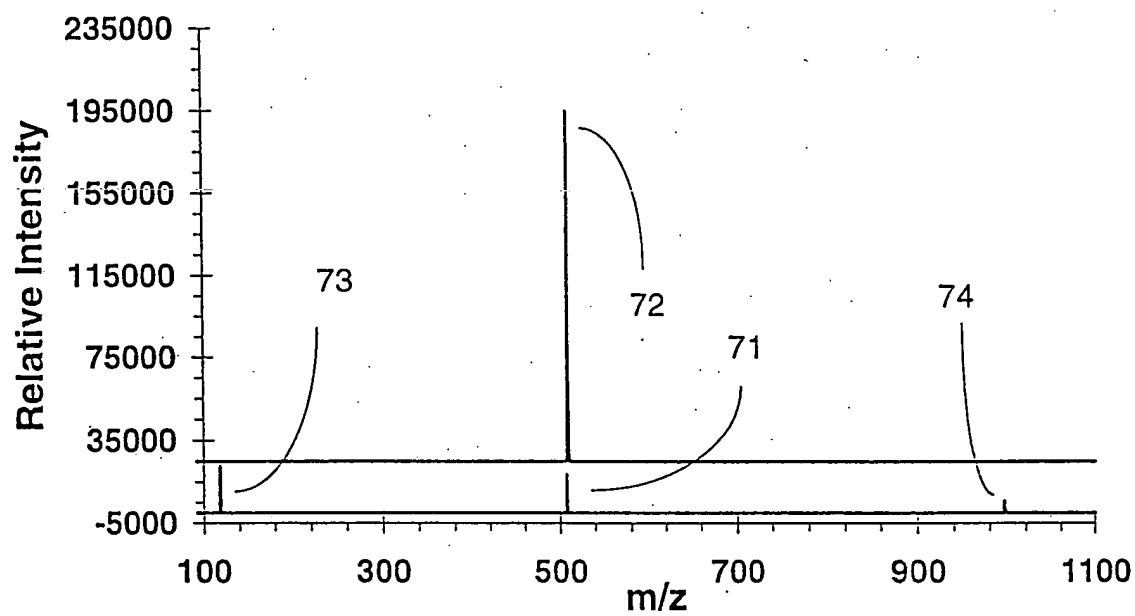


FIG. 7A

FOHTEO" 89480860

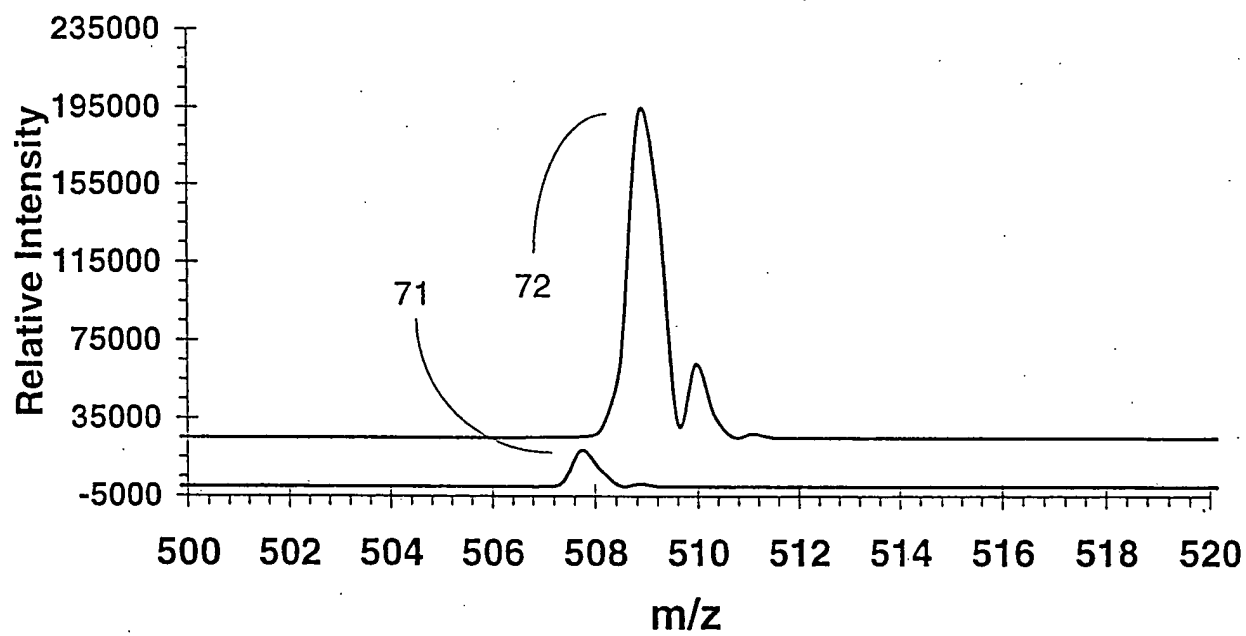
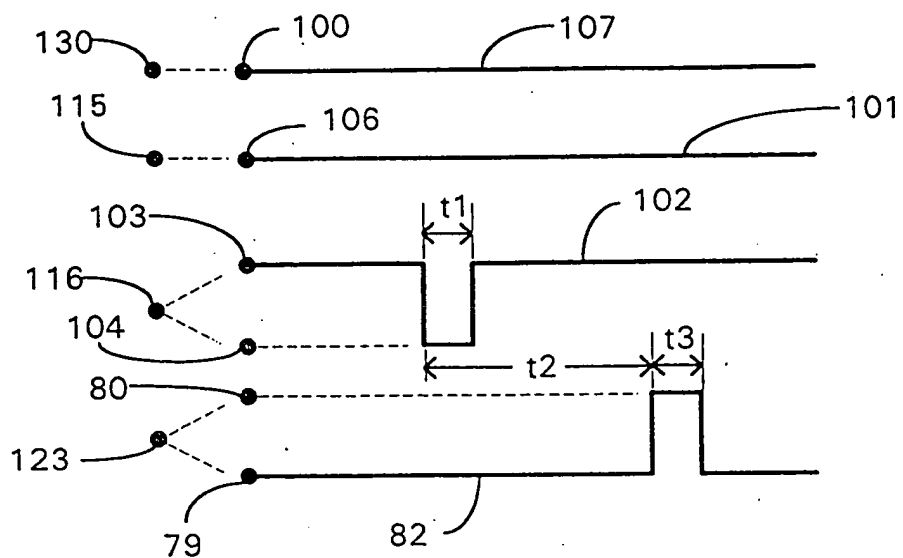
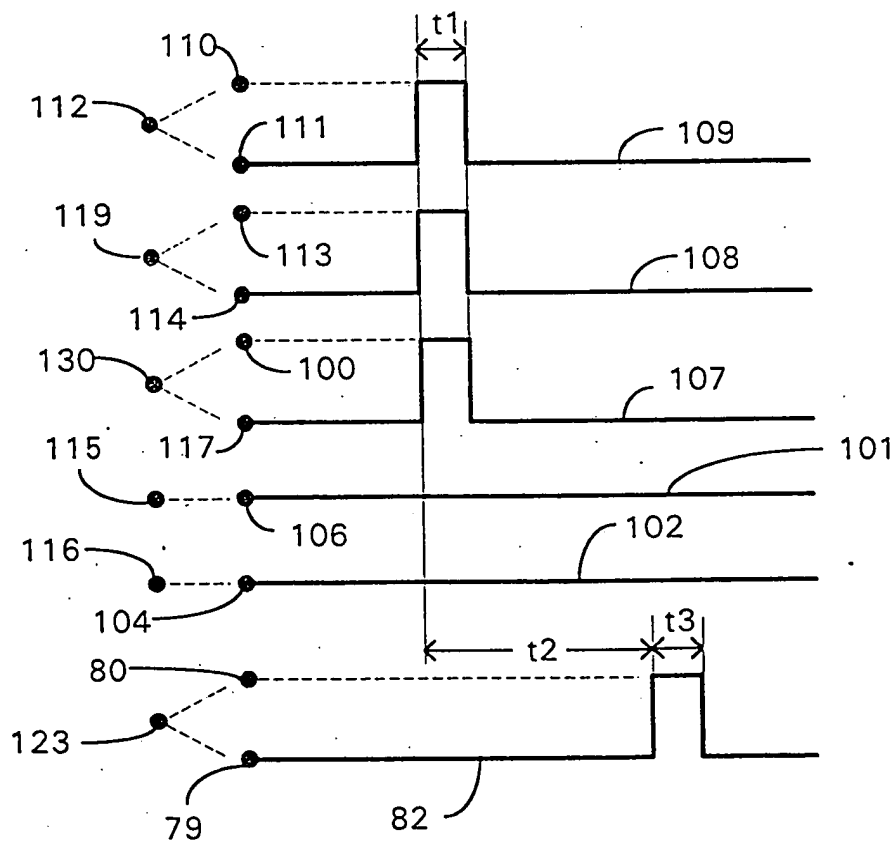


FIG. 7B



A

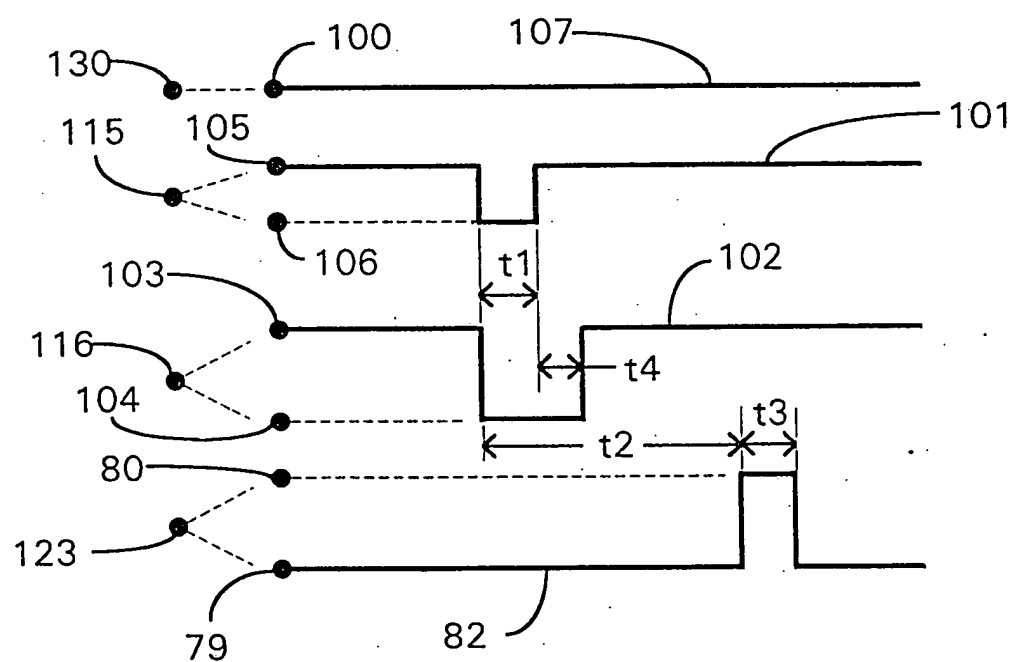


B

FIG. 9

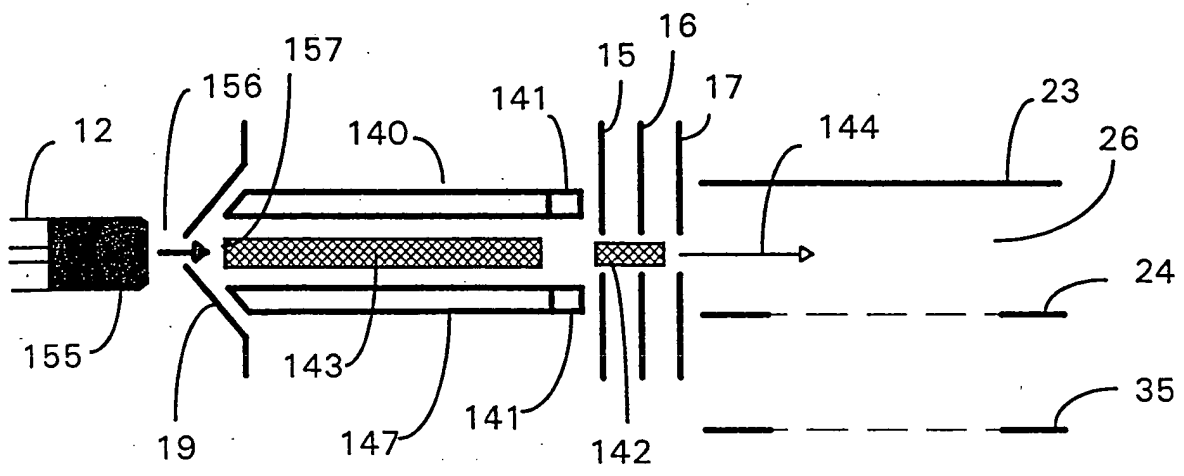
A cross-sectional view of a semiconductor device. The structure consists of several layers and regions. At the top is a layer labeled 107. Below it is a layer labeled 101. A central region is labeled 102. To the left of the central region, there are several layers and regions labeled 100, 105, 106, 103, 116, 104, 80, and 123. A dashed line labeled 130 is shown at the top left. A dashed line labeled 115 is shown below 105. A dashed line labeled 106 is shown below 103. A dashed line labeled 116 is shown below 104. A dashed line labeled 104 is shown below 116. A dashed line labeled 80 is shown below 104. A dashed line labeled 123 is shown below 80. A dashed line labeled 79 is shown at the bottom left. A dashed line labeled 82 is shown at the bottom right. A vertical dimension line labeled t_1 is shown in the center. A horizontal dimension line labeled t_2 is shown below the center. A horizontal dimension line labeled t_3 is shown at the bottom right.

A

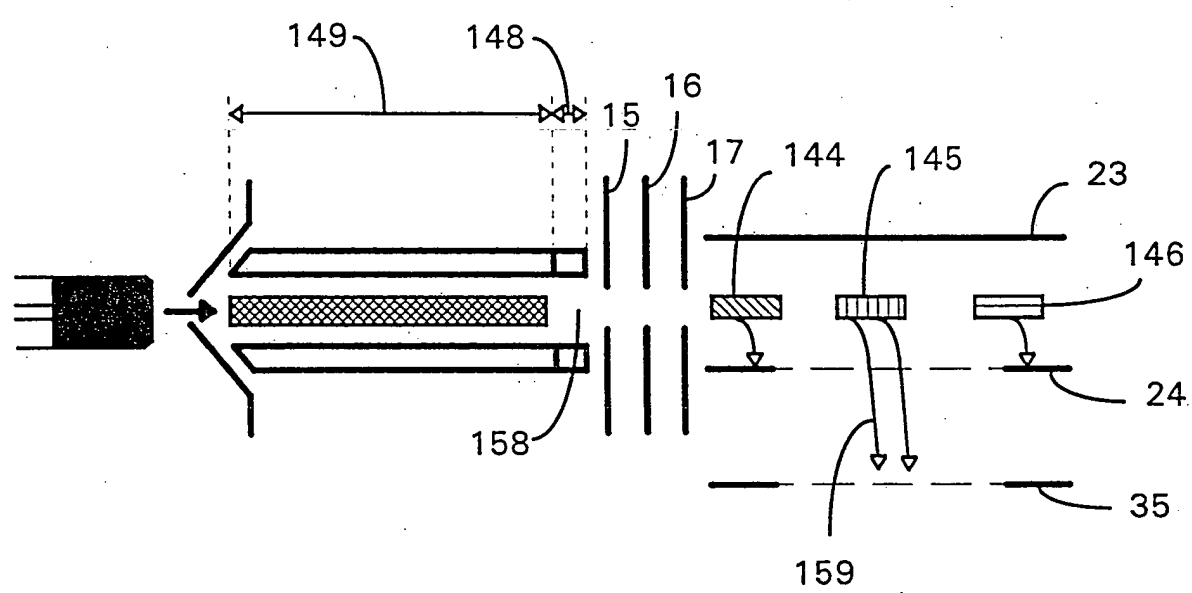


B

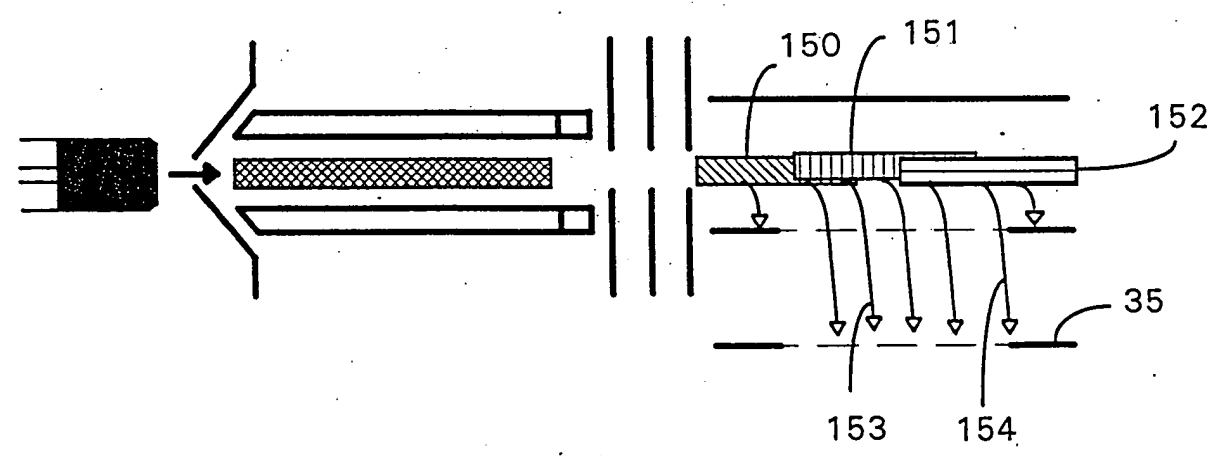
FIG. 11



A



B



C

FIG. 11